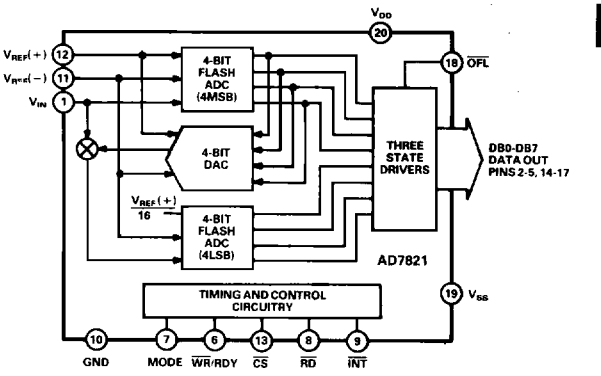
LC²MOS High Speed, µP-Compatible 8-Bit ADC with Track/Hold Function

AD7821

FEATURES

Fast Conversion Time: 660 ns max
100 kHz Track-and-Hold Function
1 MHz Sample Rate
Unipolar and Bipolar Input Ranges
Ratiometric Reference Inputs
No External Clock
Extended Temperature Range Operation
Skinny 20-Pin DIPs, SOIC and 20-Terminal Surface Mount Packages

FUNCTIONAL BLOCK DIAGRAM



GENERAL DESCRIPTION

The AD7821 is a high-speed, 8-bit, sampling, analog-to-digital converter that offers improved performance over the popular AD7820. It offers a conversion time of 660 ns (vs. 1.36 µs for the AD7820) and 100 kHz signal bandwidth (vs. 6.4 kHz). The sampling instant is better defined and occurs on the falling edge of $\overline{WR}$ or $\overline{RD}$. The provision of a V_{SS} pin (Pin 19) allows the part to operate from ±5 V supplies and to digitize bipolar input signals. Alternatively, for unipolar inputs, the V_{SS} pin can be grounded and the AD7821 will operate from a single +5 V supply, like the AD7820.

The AD7821 has a built-in track-and-hold function capable of digitizing full-scale signals up to 100 kHz max. It also uses a half-flash conversion technique that eliminates the need to generate a CLK signal for the ADC.

The AD7821 is designed with standard microprocessor control signals ($\overline{CS}$, $\overline{RD}$, $\overline{WR}$, RDY, $\overline{INT}$) and latched, three-state data outputs capable of interfacing to high-speed data buses. An overflow output ($\overline{OFL}$) is also provided for cascading devices to achieve higher resolution.

The AD7821 is fabricated in Linear-Compatible CMOS (LC²MOS), an advanced, mixed technology process combining precision bipolar circuits with low-power CMOS logic. The part features a low power dissipation of 50 mW.

PRODUCT HIGHLIGHTS

1. Fast Conversion Time
   The half-flash conversion technique, coupled with fabrication on Analog Devices' LC²MOS process, enables a very fast conversion time. The conversion time for the WR-RD mode is 660 ns, with 700 ns for the RD mode.
2. Built-In Track-and-Hold
   This allows input signals with slew rates up to 1.6 V/µs to be converted to 8-bits without an external track-and-hold. This corresponds to a 5 V peak-to-peak, 100 kHz sine-wave signal.
3. Total Unadjusted Error
   The AD7821 features an excellent total unadjusted error figure of less than ±1 LSB over the full operating temperature range.
4. Unipolar/Bipolar Input Ranges
   The AD7821 is specified for single supply (+5 V) operation with a unipolar full-scale range of 0 to +5 V, and for dual supply (±5 V) operation with a bipolar input range of ±2.5 V. Typical performance characteristics are given for other input ranges.
5. Dynamic Specifications for DSP Users
   In addition to the traditional ADC specifications, the AD7821 is specified for ac parameters, including signal-to-noise ratio, distortion and slew rate.

This is an abridged data sheet. To obtain the most recent version or complete data sheet, call our fax retrieval system at 1-800-446-6212.

AD7821—SPECIFICATIONS

V_{DD} = +5 V ± 5%, GND = 0 V. Unipolar Input Range: V_{SS} = GND, $V_{REF}(+)$ = 5 V, $V_{REF}(-)$ = GND. Bipolar Input Range: V_{SS} = −5 V ± 5%, $V_{REF}(+)$ = 2.5 V, $V_{REF}(-)$ = −2.5 V. These test conditions apply unless otherwise stated. All specifications T_{min} to T_{max} unless otherwise stated. Specifications apply for RD Mode (Pin 7 = 0 V).

Parameter	K Version[1]	B, T Versions	Units	Comments
UNIPOLAR INPUT RANGE				
Resolution[2]	8	8	Bits	
Total Unadjusted Error[3]	±1	±1	LSB max	
Minimum Resolution for which No Missing Codes are Guaranteed	8	8	Bits	
BIPOLAR INPUT RANGE				
Resolution[2]	8	8	Bits	
Zero Code Error	±1	±1	LSB max	
Full Scale Error	±1	±1	LSB max	
Signal-to-Noise Ratio (SNR)[3]	45	45	dB min	V_{IN} = 99.85 kHz Full-Scale Sine Wave with $f_{SAMPLING}$ = 500 kHz
Total Harmonic Distortion (THD)[3]	−50	−50	dB max	V_{IN} = 99.85 kHz Full-Scale Sine Wave with $f_{SAMPLING}$ = 500 kHz
Peak Harmonic or Spurious Noise[3]	−50	−50	dB max	V_{IN} = 99.85 kHz Full-Scale Sine Wave with $f_{SAMPLING}$ = 500 kHz
Intermodulation Distortion (IMD)[3]				fa (84.72 kHz) and fb (94.97 kHz) Full-Scale Sine Waves with $f_{SAMPLING}$ = 500 kHz
	−50	−50	dB max	Second Order Terms
	−50	−50	dB max	Third Order Terms
Slew Rate, Tracking[3]	1.6	1.6	V/μs max	
	2.36	2.36	V/μs typ	
REFERENCE INPUT				
Input Resistance	1.0/4.0	1.0/4.0	kΩ min/kΩ max	
V_{REF} (+) Input Voltage Range	V_{REF} (−)/V_{DD}	V_{REF} (−)/V_{DD}	V min/V max	
V_{REF} (−) Input Voltage Range	V_{SS}/V_{REF}(+)	V_{SS}/V_{REF}(+)	V min/V max	
ANALOG INPUT				
Input Voltage Range	$V_{REF}(-)$/$V_{REF}(+)$	$V_{REF}(-)$/$V_{REF}(+)$	V min/V max	
Input Leakage Current	±3	±3	μA max	$-5\ V \le V_{IN} \le +5\ V$
Input Capacitance	55	55	pF typ	
LOGIC INPUTS				
$\overline{CS}$, $\overline{WR}$, $\overline{RD}$				
V_{INH}	2.4	2.4	V min	
V_{INL}	0.8	0.8	V max	
I_{INH} ($\overline{CS}$, $\overline{RD}$)	1	1	μA max	
I_{INH} ($\overline{WR}$)	3	3	μA max	
I_{INL}	−1	−1	μA max	
Input Capacitance[4]	8	8	pF max	Typically 5 pF
MODE				
V_{INH}	3.5	3.5	V min	
V_{INL}	1.5	1.5	V max	
I_{INH}	200	200	μA max	50 μA typ
I_{INL}	−1	−1	μA max	
Input Capacitance[4]	8	8	pF max	Typically 5 pF
LOGIC OUTPUTS				
DB0–DB7, $\overline{OFL}$, $\overline{INT}$				
V_{OH}	4.0	4.0	V min	I_{SOURCE} = 360 μA
V_{OL}	0.4	0.4	V max	I_{SINK} = 1.6 mA
I_{OUT} (DB0–DB7)	±3	±3	μA max	Floating State Leakage
Output Capacitance[4] (DB0–DB7)	8	8	pF max	Typically 5 pF
RDY				
V_{OL}	0.4	0.4	V max	I_{SINK} = 2.6 mA
I_{OUT}	±3	±3	μA max	Floating State Leakage
Output Capacitance[4]	8	8	pF max	Typically 5 pF
POWER SUPPLY				
I_{DD}	15	20	mA max	$\overline{CS}$ = $\overline{RD}$ = 0 V
I_{SS}	100	100	μA max	$\overline{CS}$ = $\overline{RD}$ = 0 V
Power Dissipation	50	50	mW typ	
Power Supply Sensitivity	±1/4	±1/4	LSB max	±1/16 LSB typ, V_{DD} = 4.75 V to 5.25 V, ($V_{REF}(+)$ = 4.75 V max for Unipolar Mode)

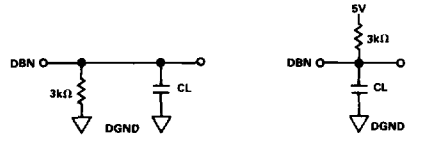
NOTES
[1]Temperature Ranges are as follows: K Version = −40°C to +85°C; B Version = −40°C to +85°C; T Version = −55°C to +125°C.
[2]1 LSB = 19.53 mV for both the unipolar (0 to +5 V) and bipolar (−2.5 V to +2.5 V) input ranges.
[3]See Terminology.
[4]Sample tested at +25°C to ensure compliance.
Specifications subject to change without notice.

TIMING CHARACTERISTICS[1] (V_{DD} = +5 V ± 5%, V_{SS} = 0 V or −5 V ± 5%; Unipolar or Bipolar Input Range)

Parameter	Limit at 25°C (All Versions)	Limit at T_{min}, T_{max} (K, B, Versions)	Limit at T_{min}, T_{max} (T Version)	Units	Conditions/Comments
t_{CSS}	0	0	0	ns min	$\overline{CS}$ to $\overline{RD}/\overline{WR}$ Setup Time
t_{CSH}	0	0	0	ns min	$\overline{CS}$ to $\overline{RD}/\overline{WR}$ Hold Time
t_{RDY}[2]	70	85	100	ns max	$\overline{CS}$ to RDY Delay. Pull-Up Resistor 5 kΩ.
t_{CRD}	700	875	975	ns max	Conversion Time (RD Mode)
t_{ACC0}[3]					Data Access Time (RD Mode)
	t_{CRD} +25	t_{CRD} +30	t_{CRD} +35	ns max	C_L = 20 pF
	t_{CRD} +50	t_{CRD} +65	t_{CRD} +75	ns max	C_L = 100 pF
t_{INTH}[2]	50	-	-	ns typ	$\overline{RD}$ to $\overline{INT}$ Delay (RD Mode)
	80	85	90	ns max	
t_{DH}[4]	15	15	15	ns min	Data Hold Time
	60	70	80	ns max	
t_P	350	425	500	ns min	Delay Time Between Conversions
t_{WR}	250	325	400	ns min	Write Pulse Width
	10	10	10	μs max	
t_{RD}	250	350	450	ns min	Delay Time between $\overline{WR}$ and $\overline{RD}$ Pulses
t_{READ1}	160	205	240	ns min	$\overline{RD}$ Pulse Width (WR-RD Mode, see Figure 12b) Determined by t_{ACC1}
t_{ACC1}[3]					Data Access Time (WR-RD Mode, see Figure 12b)
	160	205	240	ns max	C_L = 20 pF
	185	235	275	ns max	C_L = 100 pF
t_{RI}	150	185	220	ns max	$\overline{RD}$ to $\overline{INT}$ Delay
t_{INTL}[2]	380	-	-	ns typ	$\overline{WR}$ to $\overline{INT}$ Delay
	500	610	700	ns max	
t_{READ2}	65	75	85	ns min	$\overline{RD}$ Pulse Width (WR-RD Mode, see Figure 12a) Determined by t_{ACC2}
t_{ACC2}[3]					Data Access Time (WR-RD Mode, see Figure 12a)
	65	75	85	ns max	C_L = 20 pF
	90	110	130	ns max	C_L = 100 pF
t_{IHWR}[2]	80	100	120	ns max	$\overline{WR}$ to $\overline{INT}$ Delay (Stand-Alone Operation)
t_{ID}[3]					Data Access Time after $\overline{INT}$ (Stand-Alone Operation)
	30	35	40	ns max	C_L = 20 pF
	45	60	70	ns max	C_L = 100 pF

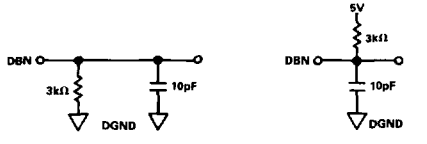
NOTES
[1]Sample tested at +25°C to ensure compliance. All input control signals are specified with tr = tf = 5 ns (10% to 90% of +5 V) and timed from a voltage level of 1.6 V.
[2]C_L = 50 pF.
[3]Measured with load circuits of Figure 1 and defined as the time required for an output to cross 0.8 V or 2.4 V.
[4]Defined as the time required for the data lines to change 0.5 V when loaded with the circuits of Figure 2.
Specifications subject to change without notice.

Test Circuits



a. High Z to V_{OH} *b. High Z to V_{OL}*

Figure 1. Load Circuits for Data Access Time Test



a. V_{OH} to High Z *b. V_{OL} to High Z*

Figure 2. Load Circuits for Data Hold Time Test

ORDERING GUIDE

Model[1]	Temperature Range	Total Unadjusted Error (LSB)	Package Option[2]
AD7821KN	−40°C to +85°C	±1 max	N-20
AD7821KP	−40°C to +85°C	±1 max	P-20A
AD7821KR	−40°C to +85°C	±1 max	R-20
AD7821BQ	−40°C to +85°C	±1 max	Q-20
AD7821TQ	−55°C to +125°C	±1 max	Q-20
AD7821TE	−55°C to +125°C	±1 max	E-20A

NOTES
[1]To order MIL-STD-883, Class B processed parts, add /883B to part number. Contact local sales office for military data sheet.
[2]E = Leadless Ceramic Chip Carrier; N = Plastic DIP; P = Plastic Leaded Chip Carrier; Q = Cerdip; R = SOIC. For outline information see Package Information section.

ABSOLUTE MAXIMUM RATINGS*

V_{DD} to GND . . . . . −0.3 V, +7 V
V_{SS} to GND . . . . . +0.3 V, 7 V
Digital Input Voltage to GND
(Pins 6-8, 13) . . . . . −0.3 V, V_{DD} +0.3 V
Digital Output Voltage to GND
(Pins 2-5, 9, 14-18) . . . . . −0.3 V, V_{DD} +0.3 V
V_{REF} (+) to GND . . . . . V_{SS} −0.3 V, V_{DD} +0.3 V
V_{REF} (−) to GND . . . . . V_{SS} −0.3 V, V_{DD} +0.3 V
V_{IN} to GND . . . . . V_{SS} −0.3 V, V_{DD} +0.3 V
Operating Temperature Range
Commercial (K Version) . . . . . −40°C to +85°C
Industrial (B Version) . . . . . −40°C to +85°C
Extended (T Version) . . . . . −55°C to +125°C
Storage Temperature Range . . . . . −65°C to +150°C
Lead Temperature (Soldering, 10secs) . . . . . +300°C
Power Dissipation (Any Package) to +75°C . . . . . 450 mW
Derates above +75°C by . . . . . 6 mW/°C

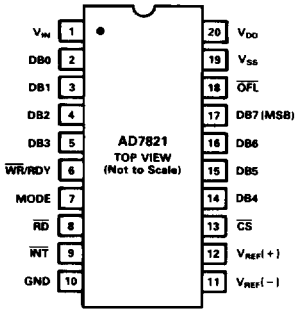
*Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

CAUTION

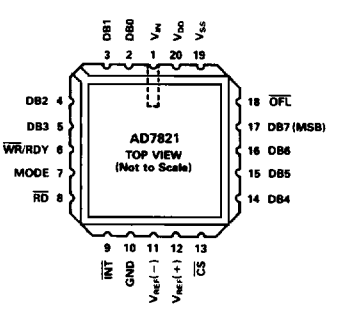
ESD (electrostatic discharge) sensitive device. The digital control inputs are diode protected; however, permanent damage may occur on unconnected devices subject to high energy electrostatic fields. Unused devices must be stored in conductive foam or shunts. The protective foam should be discharged to the destination socket before devices are inserted.

PIN CONFIGURATIONS

DIP AND SOIC



LCCC



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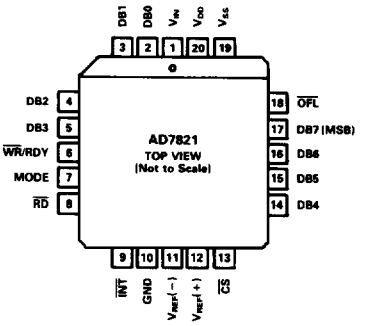

PIN FUNCTION DESCRIPTION

Pin	Mnemonic	Description
1	V_{IN}	Analog Input: Range $V_{REF}(-) \le V_{IN} \le V_{REF}(+)$.
2	DB0	Three-State Data Output (LSB).
3–5	DB1–DB3	Three-State Data Outputs.
6	$\overline{WR}$/RDY	WRITE control input/READY status output. See Digital Interface section.
7	MODE	Mode Selection Input. It determines whether the device operates in the WR-RD or RD mode. This input is internally pulled low through a 50 μA current source. See Digital Interface section.
8	$\overline{RD}$	READ Input. $\overline{RD}$ must be low to access data from the part. See Digital Interface section.
9	$\overline{INT}$	INTERRUPT Output. $\overline{INT}$ going low indicates that the conversion is complete. $\overline{INT}$ returns high on the rising edge of $\overline{CS}$ or $\overline{RD}$. See Digital Interface section.
10	GND	Ground.
11	$V_{REF}(-)$	Lower limit of reference span. Range: $V_{SS} \le V_{REF}(-) < V_{REF}(+)$.
12	$V_{REF}(+)$	Upper limit of reference span. Range: $V_{REF}(-) < V_{REF}(+) \le V_{DD}$.
13	$\overline{CS}$	Chip Select Input. The device is selected when this input is low.
14–16	DB4–DB6	Three-State Data Outputs.
17	DB7	Three-State Data Output (MSB).
18	$\overline{OFL}$	Overflow Output. If the analog input is higher than ($V_{REF}(+)$ −1/2 LSB), $\overline{OFL}$ will be low at the end of conversion. It is a non-three-state output which can be used to cascade 2 or more devices to increase resolution.
19	V_{SS}	Negative supply voltage. V_{SS} = 0 V; Unipolar Operation. V_{SS} = −5 V; Bipolar Operation.
20	V_{DD}	Positive supply voltage, +5 V.